

# Vladimir Markevich

## List of Publications by Year in descending order

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197  
papers

3,001  
citations

186265

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g-index

201  
all docs

201  
docs citations

201  
times ranked

1280  
citing authors

#	ARTICLE	IF	CITATIONS
1	Experimental Evidence of the Oxygen Dimer in Silicon. Physical Review Letters, 1998, 80, 93-96.	7.8	115
2	Vacancy–group-V-impurity atom pairs in Ge crystals doped with P, As, Sb, and Bi. Physical Review B, 2004, 70, .	3.2	108
3	Hydrogen–oxygen interaction in silicon at around 50–60°C. Journal of Applied Physics, 1998, 83, 2988-2993.	2.5	97
4	Thermal activation and deactivation of grown-in defects limiting the lifetime of float-zone silicon. Physica Status Solidi - Rapid Research Letters, 2016, 10, 443-447.	2.4	82
5	Tutorial: Junction spectroscopy techniques and deep-level defects in semiconductors. Journal of Applied Physics, 2018, 123, .	2.5	82
6	Electronic properties of antimony-vacancy complex in Ge crystals. Journal of Applied Physics, 2004, 95, 4078-4083.	2.5	77
7	Interstitial carbon-oxygen center and hydrogen related shallow thermal donors in Si. Physical Review B, 2001, 65, .	3.2	75
8	Permanent annihilation of thermally activated defects which limit the lifetime of float-zone silicon. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 2844-2849.	1.8	69
9	Electronic properties of vacancy–oxygen complex in Ge crystals. Applied Physics Letters, 2002, 81, 1821-1823.	3.3	68
10	Trivacancy and trivacancy-oxygen complexes in silicon: Experiments and ab initio modeling. Physical Review B, 2009, 80, .	3.2	55
11	Defect reactions associated with divacancy elimination in silicon. Journal of Physics Condensed Matter, 2003, 15, S2779-S2789.	1.8	52
12	Gettering of interstitial iron in silicon by plasma-enhanced chemical vapour deposited silicon nitride films. Journal of Applied Physics, 2016, 120, .	2.5	52
13	Defect engineering in Czochralski silicon by electron irradiation at different temperatures. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 121-125.	1.4	50
14	The oxygen dimer in Si: Its relationship to the light-induced degradation of Si solar cells?. Applied Physics Letters, 2011, 98, .	3.3	45
15	Vibrational absorption from vacancy-oxygen-related complexes (VO, V <sub>2</sub> O, VO <sub>2</sub> ) in irradiated silicon. Physica B: Condensed Matter, 1999, 273-274, 291-295.	2.7	44
16	Structure and properties of vacancy-oxygen complexes in Si <sub>1-x</sub> Ge <sub>x</sub> alloys. Physical Review B, 2004, 69, .	3.2	42
17	Recombination via point defects and their complexes in solar silicon. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1884-1893.	1.8	42
18	Radiation-induced shallow donors in Czochralski-grown silicon crystals saturated with hydrogen. Journal of Applied Physics, 1994, 76, 7347-7350.	2.5	38

#	ARTICLE	IF	CITATIONS
19	Identification of the mechanism responsible for the boron oxygen light induced degradation in silicon photovoltaic cells. Journal of Applied Physics, 2019, 125, .	2.5	36
20	The VO <sub>2</sub> * defect in silicon. Physica B: Condensed Matter, 2003, 340-342, 509-513.	2.7	35
21	Electronic and dynamical properties of the silicon trivacancy. Physical Review B, 2012, 86, .	3.2	35
22	Donor level of bond-center hydrogen in germanium. Physical Review B, 2004, 69, .	3.2	34
23	VO <sub>n</sub> Defects in Irradiated and Heat-Treated Silicon. Solid State Phenomena, 2005, 108-109, 267-272.	0.3	34
24	Thermal Double Donors and Quantum Dots. Physical Review Letters, 2001, 87, 235501.	7.8	33
25	Complexes of the self-interstitial with oxygen in irradiated silicon:. Physica B: Condensed Matter, 2001, 302-303, 188-192.	2.7	31
26	Interaction between self-interstitials and the oxygen dimer in silicon. Physica B: Condensed Matter, 2001, 308-310, 284-289.	2.7	31
27	Structure and electronic properties of trivacancy and trivacancy-oxygen complexes in silicon. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 568-571.	1.8	31
28	Optical Absorption due to Vibration of Hydrogen-Oxygen Pairs in Silicon. Materials Science Forum, 1995, 196-201, 915-920.	0.3	29
29	Carbon-Oxygen-Related Complexes in Irradiated and Heat-Treated Silicon: IR Absorption Studies. Solid State Phenomena, 2001, 82-84, 57-62.	0.3	28
30	Evolution of radiation-induced carbon-oxygen-related defects in silicon upon annealing: LVM studies. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 210-213.	1.4	27
31	Tin-vacancy complex in germanium. Journal of Applied Physics, 2011, 109, .	2.5	27
32	New infrared absorption bands related to interstitial oxygen in silicon. Journal of Applied Physics, 1998, 84, 2466-2470.	2.5	26
33	Thermal double donor annihilation and oxygen precipitation at around 650°C in Czochralski-grown Si: local vibrational mode studies. Journal of Physics Condensed Matter, 2005, 17, S2237-S2246.	1.8	25
34	Energy state distributions of the Pb centers at the (100), (110), and (111) Si•SiO <sub>2</sub> interfaces investigated by Laplace deep level transient spectroscopy. Applied Physics Letters, 2008, 92, .	3.3	25
35	The Oxygen Dimer in Silicon: Some Experimental Observations. Materials Science Forum, 1997, 258-263, 361-366.	0.3	23
36	Evidence for trapped by carbon impurities in silicon. Physica B: Condensed Matter, 2001, 308-310, 197-201.	2.7	23

#	ARTICLE	IF	CITATIONS
37	Radiation-induced defects and their transformations in oxygen-rich germanium crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 702-706.	0.8	23
38	Formation of interstitial carbon–interstitial oxygen complexes in silicon: Local vibrational mode spectroscopy and density functional theory. <i>Physical Review B</i> , 2008, 78, .	3.2	23
39	Boron–Oxygen Complex Responsible for Light-Induced Degradation in Silicon Photovoltaic Cells: A New Insight into the Problem. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900315.	1.8	23
40	Observation and theory of the $V_{Si}O_{H2}$ complex in silicon. <i>Physical Review B</i> , 2000, 61, 12964-12969.	3.2	22
41	Vacancy–oxygen complex in $Si_{1-x}Ge_x$ crystals. <i>Applied Physics Letters</i> , 2003, 82, 2652-2654.	3.3	22
42	Evolution of vacancy-related defects upon annealing of ion-implanted germanium. <i>Physical Review B</i> , 2008, 78, .	3.2	22
43	Formation of Oxygen Dimers in Silicon during Electron-Irradiation Above 250 Å°C. <i>Materials Science Forum</i> , 1997, 258-263, 367-372.	0.3	21
44	Titanium in silicon: Lattice positions and electronic properties. <i>Applied Physics Letters</i> , 2014, 104, 152105.	3.3	20
45	A comparative study of ion implantation and irradiation-induced defects in Ge crystals. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 589-596.	4.0	19
46	Passivation of titanium by hydrogen in silicon. <i>Applied Physics Letters</i> , 2013, 103, 132103.	3.3	19
47	Evidence for an iron-hydrogen complex in p-type silicon. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	19
48	Acceptor levels of the carbon vacancy in 4H-SiC: Combining Laplace deep level transient spectroscopy with density functional modeling. <i>Journal of Applied Physics</i> , 2018, 124, 245701.	2.5	19
49	Thermally activated defects in float zone silicon: Effect of nitrogen on the introduction of deep level states. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	19
50	Characterisation of negative-U defects in semiconductors. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 323001.	1.8	19
51	Cs–H <sub>2</sub> * defect in crystalline silicon. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 220-226.	2.7	18
52	Vacancy–oxygen complex in Ge crystals. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 844-848.	2.7	17
53	The vacancy–donor pair in unstrained silicon, germanium and SiGe alloys. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2293-S2302.	1.8	17
54	Implantation defects and n-type doping in Ge and Ge rich SiGe. <i>Thin Solid Films</i> , 2008, 517, 152-154.	1.8	17

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55	Emission and Capture Kinetics for a Hydrogen-Related Negative-U Center in Silicon: Evidence for Metastable Neutral Charge State. <i>Materials Science Forum</i> , 1997, 258-263, 217-222.	0.3	16
56	Electrically active radiation-induced defects in Czochralski-grown Si with low carbon content. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2331-S2340.	1.8	16
57	Bistability and electrical activity of the vacancy-dioxygen complex in silicon. <i>Semiconductors</i> , 2006, 40, 1282-1286.	0.5	15
58	EPR Study of Hydrogen-Related Radiation-Induced Shallow Donors in Silicon. <i>Physica Status Solidi (B): Basic Research</i> , 1998, 210, 545-549.	1.5	14
59	Vacancy-related complexes in neutron-irradiated silicon. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2229-S2235.	1.8	14
60	Interstitial Carbon Related Defects in Low-Temperature Irradiated Si: FTIR and DLTS Studies. <i>Solid State Phenomena</i> , 2005, 108-109, 261-266.	0.3	14
61	Determination of interstitial oxygen concentration in germanium by infrared absorption. <i>Journal of Applied Physics</i> , 2006, 100, 033525.	2.5	14
62	Electron emission and capture by oxygen-related bistable thermal double donors in silicon studied with junction capacitance techniques. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	14
63	Local vibrational modes of the oxygen-vacancy complex in germanium. <i>Semiconductors</i> , 2002, 36, 621-624.	0.5	13
64	Defect-impurity interactions in irradiated tin-doped Cz-Si crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 694-697.	0.8	13
65	Saddle point for oxygen reorientation in the vicinity of a silicon vacancy. <i>Physical Review B</i> , 2003, 67, .	3.2	13
66	Metastable VO <sub>2</sub> Complexes in Silicon: Experimental and Theoretical Modeling Studies. <i>Solid State Phenomena</i> , 2005, 108-109, 223-228.	0.3	13
67	Radiation-Induced Defect Reactions in Cz-Si Crystals Contaminated with Cu. <i>Solid State Phenomena</i> , 2008, 131-133, 363-368.	0.3	13
68	Laplace deep level transient spectroscopy: Embodiment and evolution. <i>Physica B: Condensed Matter</i> , 2012, 407, 3026-3030.	2.7	13
69	Donor levels of the divacancy-oxygen defect in silicon. <i>Journal of Applied Physics</i> , 2014, 115, 012004.	2.5	13
70	Powerful recombination centers resulting from reactions of hydrogen with carbon-oxygen defects in n-type Czochralski-grown silicon. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1700133.	2.4	13
71	New insights into the thermally activated defects in n-type float-zone silicon. <i>AIP Conference Proceedings</i> , 2019, , .	0.4	13
72	Metastability and Negative-U Properties for Hydrogen-Related Radiation-Induced Defect in Silicon. <i>Materials Science Forum</i> , 1995, 196-201, 945-950.	0.3	12

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73	Ion implantation and electron irradiation damage in unstrained germanium and silicon-germanium alloys. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 166-169.	3.5	12
74	$E_1$ / $E_2$ traps in 6H-SiC studied with Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	12
75	Kinetics of Bulk Lifetime Degradation in Float-Zone Silicon: Fast Activation and Annihilation of Crown Defects and the Role of Hydrogen versus Light. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2000436.	1.8	12
76	New Infrared Vibrational Bands Related to Interstitial and Substitutional Oxygen in Silicon. <i>Solid State Phenomena</i> , 1999, 69-70, 309-314.	0.3	11
77	Oxygen and Carbon Clustering in Cz-Si during Electron Irradiation at Elevated Temperatures. <i>Solid State Phenomena</i> , 1999, 69-70, 297-302.	0.3	11
78	Local vibrational mode spectroscopy of thermal donors in germanium. <i>Physica B: Condensed Matter</i> , 1999, 273-274, 570-574.	2.7	11
79	Interaction of hydrogen (deuterium) molecules with interstitial oxygen atoms in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999, 58, 26-30.	3.5	11
80	Early stages of oxygen clustering in hydrogenated Cz-Si: IR absorption studies. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 180-187.	2.7	11
81	Defect reactions associated with the dissociation of the phosphorus-vacancy pair in silicon. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 513-516.	2.7	11
82	Divacancy-Oxygen and Trivacancy-Oxygen Complexes in Silicon: Local Vibrational Mode Studies. <i>Solid State Phenomena</i> , 0, 156-158, 129-134.	0.3	11
83	Trivacancy-oxygen complex in silicon: Local vibrational mode characterization. <i>Physica B: Condensed Matter</i> , 2009, 404, 4568-4571.	2.7	11
84	Recombination via transition metals in solar silicon: The significance of hydrogen-metal reactions and lattice sites of metal atoms. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700304.	1.8	11
85	Electronic Properties and Structure of a Complex Incorporating a Self-Interstitial and two Oxygen Atoms in Silicon. <i>Solid State Phenomena</i> , 2005, 108-109, 273-278.	0.3	10
86	Radiation-induced bistable centers with deep levels in silicon n-p structures. <i>Semiconductors</i> , 2016, 50, 751-755.	0.5	10
87	Silicon incorporation in a shallow donor center in hydrogenated Czochralski-grown Si crystals: An EPR study. <i>Physical Review B</i> , 1997, 56, R12695-R12697.	3.2	9
88	Spectroscopic observation of the TDD0 in silicon. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 1046-1050.	2.7	9
89	Electric field enhancement of electron emission from deep level traps in Ge crystals. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 200-203.	2.7	9
90	Impedance and barrier capacitance of silicon diodes implanted with high-energy Xe ions. <i>Microelectronics Reliability</i> , 2010, 50, 813-820.	1.7	9

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91	Exceptional gettering response of epitaxially grown kerfless silicon. Journal of Applied Physics, 2016, 119, .	2.5	9
92	Direct observation of hydrogen at defects in multicrystalline silicon. Progress in Photovoltaics: Research and Applications, 2021, 29, 1158-1164.	8.1	9
93	Isotopic effects on vibrational modes of thermal double donors in Si and Ge. Physica B: Condensed Matter, 2001, 308-310, 290-293.	2.7	8
94	Carbon-related centres in irradiated SiGe alloys. Physica B: Condensed Matter, 2003, 340-342, 823-826.	2.7	8
95	Oxygen-related radiation-induced defects in SiGe alloys. Journal of Physics Condensed Matter, 2003, 15, S2835-S2842.	1.8	8
96	Trivacancy in silicon: A combined DLTS and ab-initio modeling study. Physica B: Condensed Matter, 2009, 404, 4565-4567.	2.7	8
97	Structure, Electronic Properties and Annealing Behavior of Di-Interstitial-Oxygen Center in Silicon. Solid State Phenomena, 0, 242, 290-295.	0.3	8
98	Electrical Characterization of Thermally Activated Defects in n-Type Float-Zone Silicon. IEEE Journal of Photovoltaics, 2021, 11, 26-35.	2.5	8
99	Thermal Double Donors in Silicon: A New Insight into the Problem. , 1996, , 329-336.		8
100	Thermal Donor Formation and Mechanism of Enhanced Oxygen Diffusion in Silicon. Materials Science Forum, 1989, 38-41, 589-594.	0.3	7
101	Over-coordinated oxygen in the interstitial carbon-oxygen complex. Physica B: Condensed Matter, 2001, 308-310, 305-308.	2.7	7
102	Publisher's Note: Donor level of bond-center hydrogen in germanium [Phys. Rev. B69, 245207 (2004)]. Physical Review B, 2004, 70, .	3.2	7
103	Understanding Ion Implantation Defects in Germanium. ECS Transactions, 2006, 3, 67-76.	0.5	7
104	Molybdenum nano-precipitates in silicon: A TEM and DLTS study. Physica Status Solidi (B): Basic Research, 2014, 251, 2201-2204.	1.5	7
105	Electronic Properties and Structure of Boron-Hydrogen Complexes in Crystalline Silicon. Solar Rrl, 2022, 6, 2100459.	5.8	7
106	Dynamics of Hydrogen in Silicon at Finite Temperatures from First Principles. Physica Status Solidi (B): Basic Research, 2022, 259, .	1.5	7
107	Local vibrational mode bands due to a DX-like hydrogen-related center in silicon. Journal of Applied Physics, 1998, 84, 1246-1250.	2.5	6
108	Enhanced formation of thermal donors in irradiated germanium: Local vibrational mode spectroscopy. Semiconductors, 1999, 33, 1163-1165.	0.5	6

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109	Electronic Properties and Thermal Stability of Defects Induced by MeV Electron/Ion Irradiations in Unstrained Germanium and SiGe Alloys. <i>Solid State Phenomena</i> , 2005, 108-109, 253-260.	0.3	6
110	Electron- and hole-related electrical activity of InAs/GaAs quantum dots. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 580-583.	2.7	6
111	Interactions of Self-Interstitials with Interstitial Carbon-Interstitial Oxygen Center in Irradiated Silicon: An Infrared Absorption Study. <i>Solid State Phenomena</i> , 0, 205-206, 218-223.	0.3	6
112	Interactions of hydrogen with vanadium in crystalline silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 2838-2843.	1.8	6
113	Theory of a carbon-oxygen-hydrogen recombination center in $\alpha$ -Si. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700309.	1.8	6
114	The di-interstitial in silicon: Electronic properties and interactions with oxygen and carbon impurity atoms. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700261.	1.8	6
115	Optical Properties and the Mechanism of the Formation of V2O2 and V3O2 Vacancy-oxygen Complexes in Irradiated Silicon Crystals. <i>Semiconductors</i> , 2018, 52, 1097-1103.	0.5	6
116	Passivation of thermally-induced defects with hydrogen in float-zone silicon. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 275105.	2.8	6
117	Photoluminescence characterization of defects created in electron-irradiated silicon at elevated temperatures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 72, 146-149.	3.5	5
118	Early stages of oxygen precipitation in silicon: The effect of hydrogen. <i>Semiconductors</i> , 2000, 34, 998-1003.	0.5	5
119	Hydrogen-plasma-enhanced oxygen precipitation in silicon. <i>Journal of Physics Condensed Matter</i> , 2000, 12, 10145-10152.	1.8	5
120	Electronic properties of vacancy-oxygen complexes in SiGe alloys. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 790-794.	2.7	5
121	Interaction of self-interstitials with oxygen-related defects in electron-irradiated Ge crystals. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 613-618.	4.0	5
122	Iron-aluminium pair reconfiguration processes in SiGe alloys. <i>Journal of Materials Science: Materials in Electronics</i> , 2007, 18, 759-762.	2.2	5
123	Complexes of self-interstitials with oxygen atoms in germanium. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 344-347.	4.0	5
124	Interactions of Cu and Ni Impurities with Vacancy-related Point Defects in Czochralski-grown Si Crystals. <i>ECS Transactions</i> , 2009, 18, 1013-1018.	0.5	5
125	Local vibrational modes of the oxygen trimer in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 709-712.	0.8	5
126	Local vibrational modes of interstitial boron-interstitial oxygen complex in silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 2850-2854.	1.8	5



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127	Radiation-induced interstitial carbon atom in silicon: Effect of charge state on annealing characteristics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700262.	1.8	5
128	Effect of Hydrogen on Oxygen-Related Defect Reactions in Silicon at Elevated Temperatures. , 1996, , 103-122.		5
129	Acceptor-oxygen defects in silicon: The electronic properties of centers formed by boron, gallium, indium, and aluminum interactions with the oxygen dimer. <i>Journal of Applied Physics</i> , 2021, 130, 245703.	2.5	5
130	Calibration Factor for Determination of Interstitial Oxygen Concentration in Germanium by Infrared Absorption. <i>Solid State Phenomena</i> , 2005, 108-109, 735-740.	0.3	4
131	Germanium – The Semiconductor of Tomorrow?. <i>AIP Conference Proceedings</i> , 2006, , .	0.4	4
132	Hydrogen-related shallow donors in Ge crystals implanted with protons. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 629-633.	4.0	4
133	Identification of stable and metastable forms of centers in germanium. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 192-195.	2.7	4
134	Electrically active defects induced by hydrogen and helium implantations in Ge. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 354-359.	4.0	4
135	Formation of Radiation-Induced Defects in Si Crystals Irradiated with Electrons at Elevated Temperatures. <i>Solid State Phenomena</i> , 0, 156-158, 299-304.	0.3	4
136	Interstitial-related defect reactions in electron-irradiated oxygen-rich Ge crystals: A DLTS study. <i>Physica B: Condensed Matter</i> , 2009, 404, 4533-4536.	2.7	4
137	Radiation-Induced Defect Reactions in Tin-Doped Ge Crystals. <i>Solid State Phenomena</i> , 0, 178-179, 392-397.	0.3	4
138	Divacancy-iron complexes in silicon. <i>Journal of Applied Physics</i> , 2013, 113, 044503.	2.5	4
139	Recombination centers resulting from reactions of hydrogen and oxygen in n-type Czochralski silicon. , 2016, , .		4
140	Vanadium in silicon: Lattice positions and electronic properties. <i>Applied Physics Letters</i> , 2017, 110, 142105.	3.3	4
141	Lifetime degradation of n-type Czochralski silicon after hydrogenation. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	4
142	Infrared Vibrational Bands Related to Thermal Donors in Germanium. <i>Solid State Phenomena</i> , 1999, 69-70, 303-308.	0.3	3
143	Vibration modes of oxygen dimers in germanium. <i>Semiconductors</i> , 2001, 35, 864-869.	0.5	3
144	Phonon-assisted changes in charge states of deep level defects in germanium. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 61-65.	2.7	3

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145	Oxygen loss and thermal double donor formation in germanium. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 619-624.	4.0	3
146	High-resolution DLTS of vacancy–donor pairs in P-, As- and Sb-doped silicon. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 73-76.	2.7	3
147	Vacancy defect reactions associated with oxygen and bismuth in irradiated germanium. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 93-96.	2.7	3
148	Vacancy Clusters in Germanium. <i>Solid State Phenomena</i> , 0, 131-133, 125-130.	0.3	3
149	Electrically active defects induced by irradiations with electrons, neutrons and ions in Ge-rich SiGe alloys. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 184-187.	2.7	3
150	Effect of high-temperature heat treatment on the generation and annealing of radiation-induced defects in n-type silicon crystals. <i>Inorganic Materials</i> , 2007, 43, 1153-1159.	0.8	3
151	Electrically active hydrogen-implantation-induced defects in Ge crystals and SiGe alloys. <i>Thin Solid Films</i> , 2008, 517, 419-421.	1.8	3
152	The Trivacancy and Trivacancy-Oxygen Family of Defects in Silicon. <i>Solid State Phenomena</i> , 0, 205-206, 181-190.	0.3	3
153	Evidence for Molybdenum–Hydrogen Bonding in p-Type Silicon upon Annealing under Illumination. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800611.	1.8	3
154	Interaction of Radiation-Induced Self-Interstitials with Vacancy–Oxygen Related Defects $V_n O_2$ ( $n$ from 1 to 8) / Overl...	1.8	3
155	On the Correlation between Light-Induced Degradation and Minority Carrier Traps in Boron-Doped Czochralski Silicon. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 6140-6146.	8.0	3
156	Interaction of Hydrogen with Radiation-Induced Defects in Cz-Si Crystals. <i>Solid State Phenomena</i> , 1999, 69-70, 403-408.	0.3	2
157	Local vibrational mode bands of V–O–H complexes in silicon. <i>Physica B: Condensed Matter</i> , 1999, 273-274, 300-304.	2.7	2
158	Effect of high-temperature electron irradiation on the formation of radiative defects in silicon. <i>Physica B: Condensed Matter</i> , 1999, 273-274, 528-531.	2.7	2
159	Response to “Comment on “Hydrogen–oxygen interaction in silicon at around 50 °C” [J. Appl. Phys. 82, 4635 (2000)]. <i>Journal of Applied Physics</i> , 2000, 87, 4637-4637.	2.5	2
160	Enhancement of thermal donor formation in germanium by preliminary irradiation: infrared absorption measurements. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 201-205.	2.7	2
161	Magnetic resonance and FTIR studies of shallow donor centers in hydrogenated Cz-silicon. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 253-256.	2.7	2
162	Stable Hydrogen Pair Trapped at Carbon Impurities in Silicon. <i>Defect and Diffusion Forum</i> , 2003, 221-223, 1-10.	0.4	2

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163	Recombination and radiation damage in crystalline silicon solar cell material. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2274-2281.	0.8	2
164	The different behaviour of $\text{CiO}_i$ and $\text{CiCs}$ defects in SiGe. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 58-61.	4.0	2
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